Vishay Semiconductors

Phase Control Thyristors (Stud Version), 110 A



PRODUCT SUMMARY			
I _{T(AV)}	110 A		
V_{DRM}/V_{RRM}	400 V, 800 V, 1200 V		
V_{TM}	1.57 V		
l _{GT}	80 mA		
T_J	-40 °C to 140 °C		
Package	TO-209AC (TO-94)		
Diode variation	Single SCR		

FEATURES

- High current and high surge ratings
- · Hermetic ceramic housing



RoHS COMPLIANT

 Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		110	A		
I _{T(AV)}	T _C	90	°C		
I _{T(RMS)}		172			
1	50 Hz	2080	Α		
I _{TSM}	60 Hz	2180			
l ² t	50 Hz	21.7	kA ² s		
1-1	60 Hz	19.8	KA-S		
V _{DRM} /V _{RRM}		400 to 1200	V		
t _q	Typical	110	μs		
T _J		-40 to 140	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGI	VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA					
	40	400	500						
VS-110RKI VS-111RKI	80	800	900	20					
	120	1200	1300						



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ABSOLUTE MAXIMUM RATING	S						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS	
Maximum average on-state current at case temperature	I _{T(AV)}	180° condu	180° conduction, half sine wave			A °C	
<u> </u>		DO 100.00	 		90	10	
Maximum RMS on-state current	I _{T(RMS)}		case temperat	ure	172		
		t = 10 ms	No voltage		2080		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		2180	Α	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		1750		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1830		
Maximum I ² t for fusing		t = 10 ms	No voltage	initial T _J = T _J maximum	21.7	kA ² s	
	l ² t	t = 8.3 ms	reapplied		19.8		
		t = 10 ms	100 % V _{RRM}		15.3		
		t = 8.3 ms	reapplied		14.0		
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to	t = 0.1 ms to 10 ms, no voltage reapplied			kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.82	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			2.16	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			1.70	1115.2	
Maximum on-state voltage	V_{TM}	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.57	V	
Maximum holding current	I _H	T 05.00 I I OV 1.11 I		V registive lead	200	A	
Typical latching current	ΙL	$T_J = 25$ °C, anode supply 6 V resistive load 400		400	mA		

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	300	A/μs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1	0
Typical turn-off time	tq	I_{TM} = 50 A, T_J = T_J maximum, dl/dt = - 5 A/µs V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 25 Ω	110	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	20	mA



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TRIGGERING						
DADAMETER	SYMBOL	TEST COMPLETIONS		VALUES		UNITS
PARAMETER	SYMBOL	1531	CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	12		w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	3	.0] vv
Maximum peak positive gate current	I _{GM}			3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	2	20	
Maximum peak negative gate voltage	- V _{GM}			10		- V
DC gate current required to trigger	C gate current required to trigger	T _J = - 40 °C	Maximum required gate trigger/current/voltage are the lowest value which will	180	-	
		T _J = 25 °C		80	120	mA
		T _J = 140 °C		40	-	
		T _J = - 40 °C	trigger all units 12 V anode	2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	to cathode applied	1.6	2	2 V
		T _J = 140 °C		1	-	
DC gate current not to trigger	I _{GD}	T. T. maximum	Maximum gate current/ voltage not to trigger is the maximum value which will			
DC gate voltage not to trigger	V_{GD}	$T_J = T_J \text{ maximum}$	not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 140	°C		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.27	7 K/W		
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.1			
Mounting torque + 10.0/		Non-lubricated threads	15.5 (137)	N · m		
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)		
Approximate weight			130	g		
Case style		See dimensions - link at the end of datasheet TO-209AC (To		(TO-94)		

△R _{thJC} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS		
180°	0.043	0.031				
120°	0.052	0.053				
90°	0.066	0.071	$T_J = T_J \text{ maximum}$	K/W		
60°	0.096	0.101				
30°	0.167	0.169				

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



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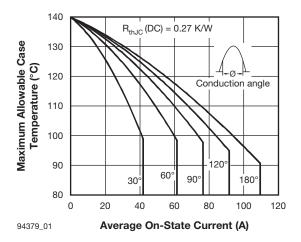


Fig. 1 - Current Ratings Characteristics

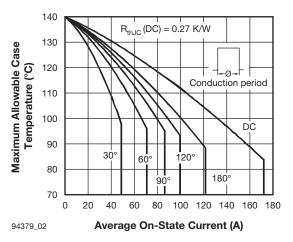
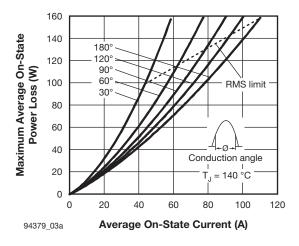


Fig. 2 - Current Ratings Characteristics



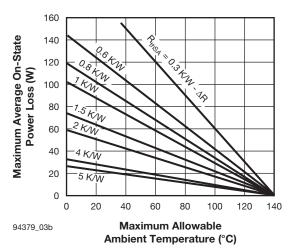
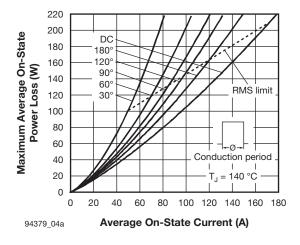


Fig. 3 - On-State Power Loss Characteristics



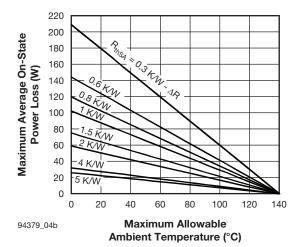


Fig. 4 - On-State Power Loss Characteristics



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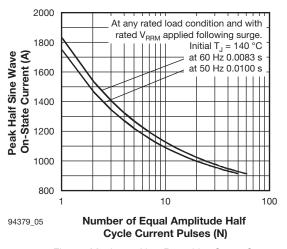


Fig. 5 - Maximum Non-Repetitive Surge Current

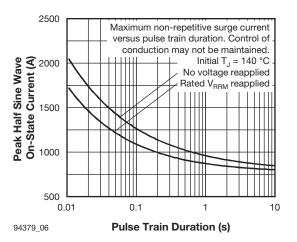


Fig. 6 - Maximum Non-Repetitive Surge Current

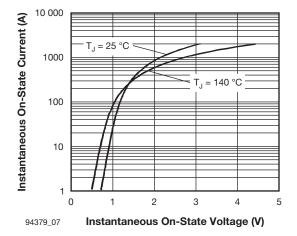


Fig. 7 - On-State Voltage Drop Characteristics

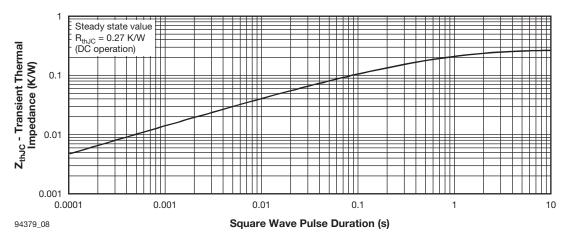


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

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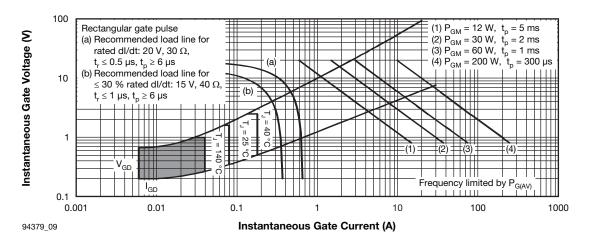
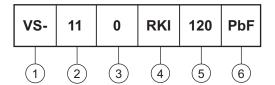


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 I_{T(AV)} rated average output current (rounded/10)
- 0 = Eyelet terminals (gate and auxiliary cathode leads)
 - 1 = Fast-on terminals (gate and auxiliary cathode leads)
- 4 Thyristor
- 5 Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 6 None = Standard production
 - PbF = Lead (Pb)-free

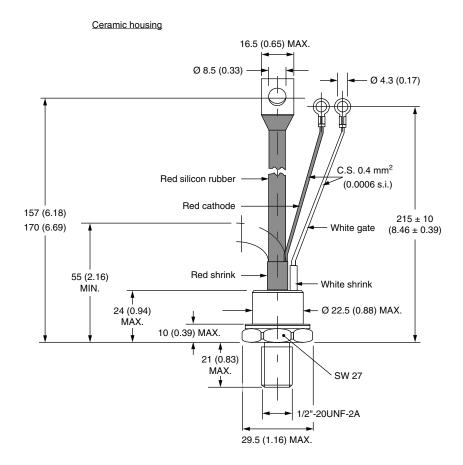
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95003

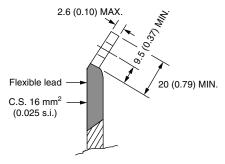


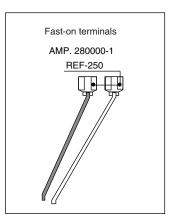
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TO-209AC (TO-94) for 110RKI and 111RKI Series

DIMENSIONS in millimeters (inches)







Note

• For metric device: M12 x 1.75 contact factory



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